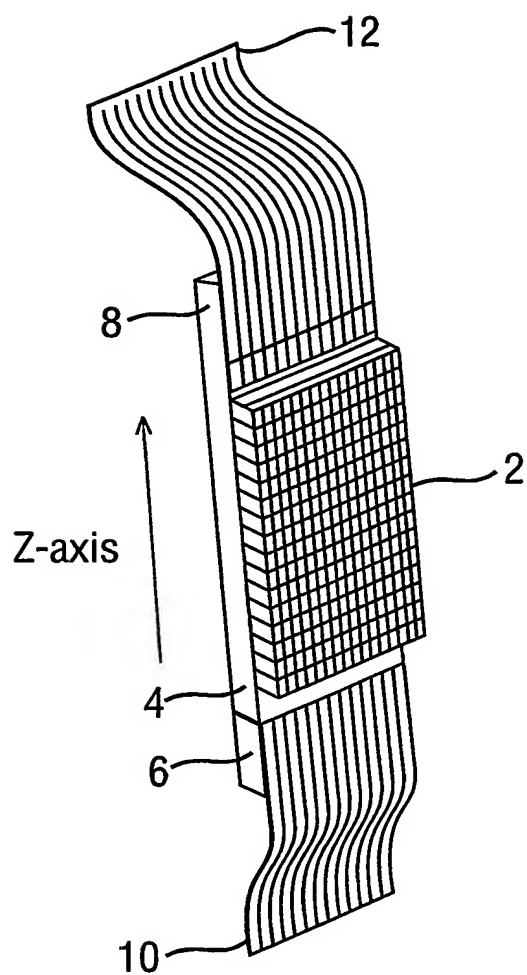


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FIG. 1



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FIG. 2

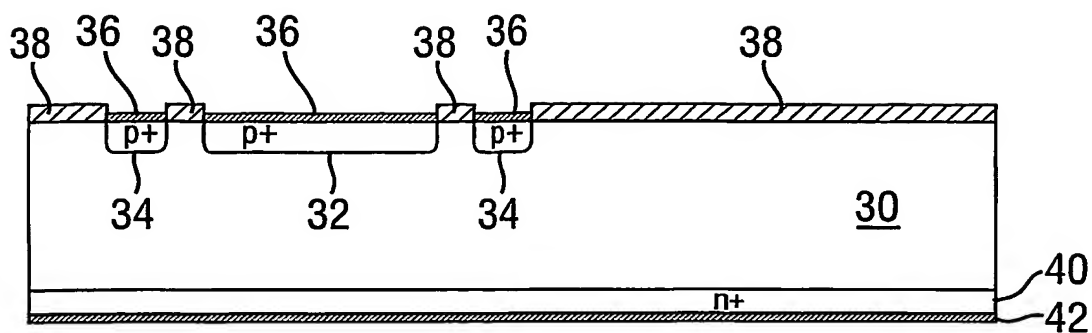


FIG. 3

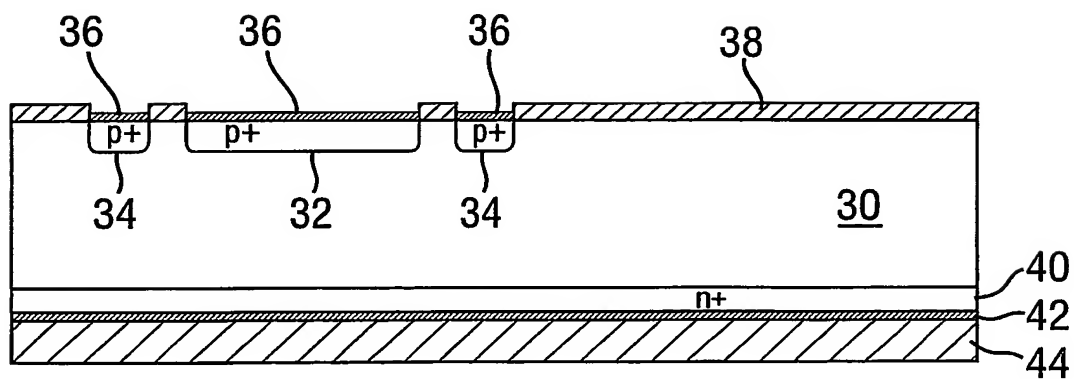
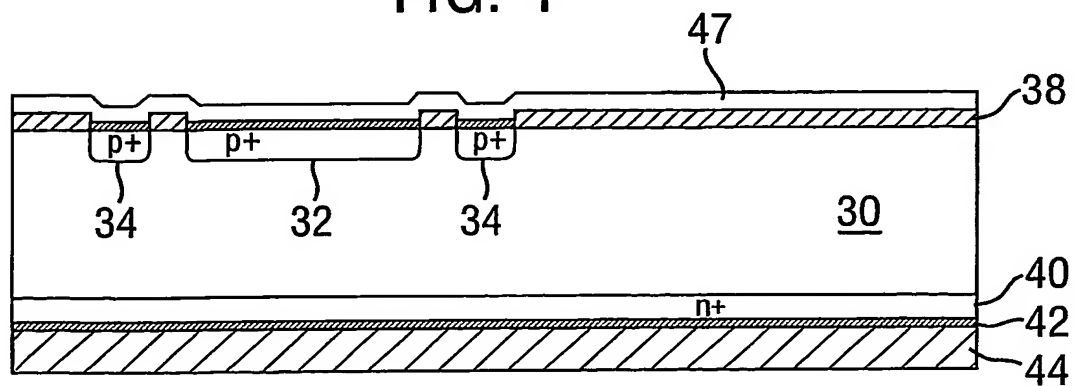


FIG. 4



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FIG. 5

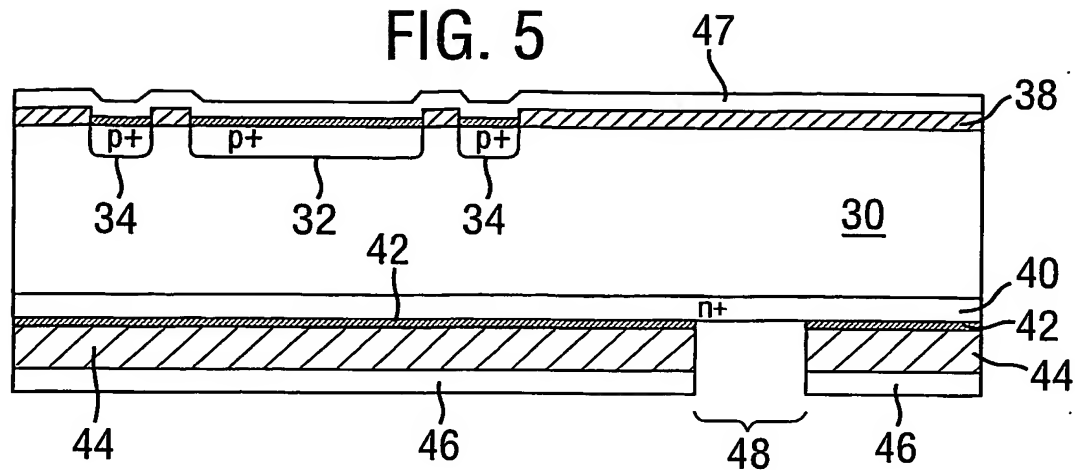


FIG. 6

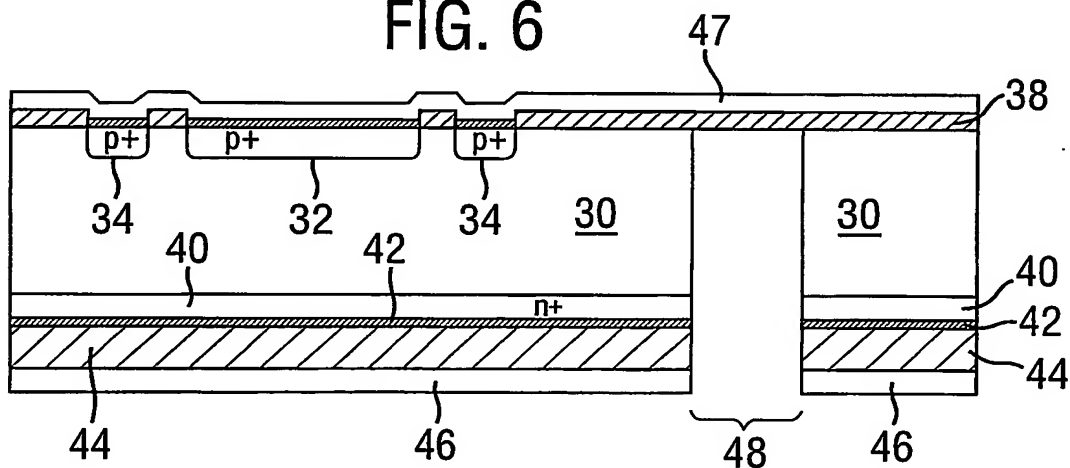
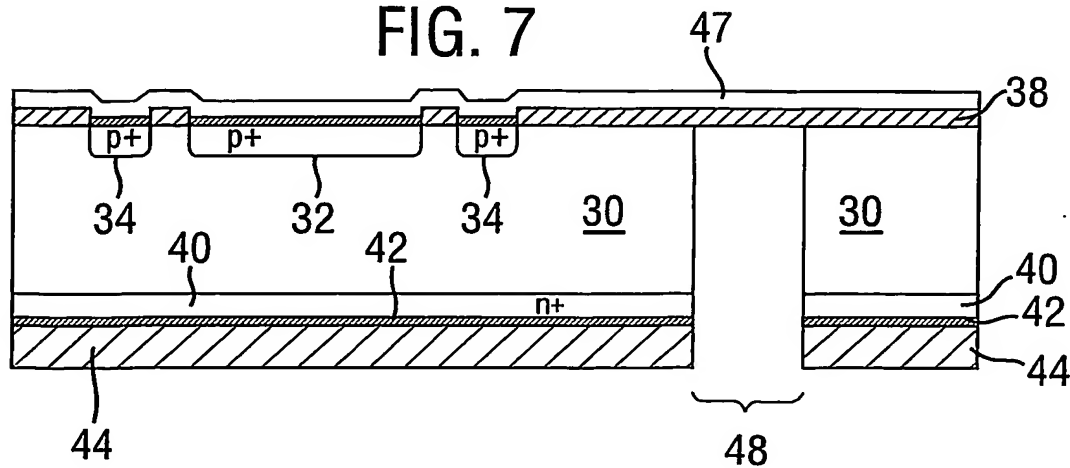


FIG. 7



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FIG. 8

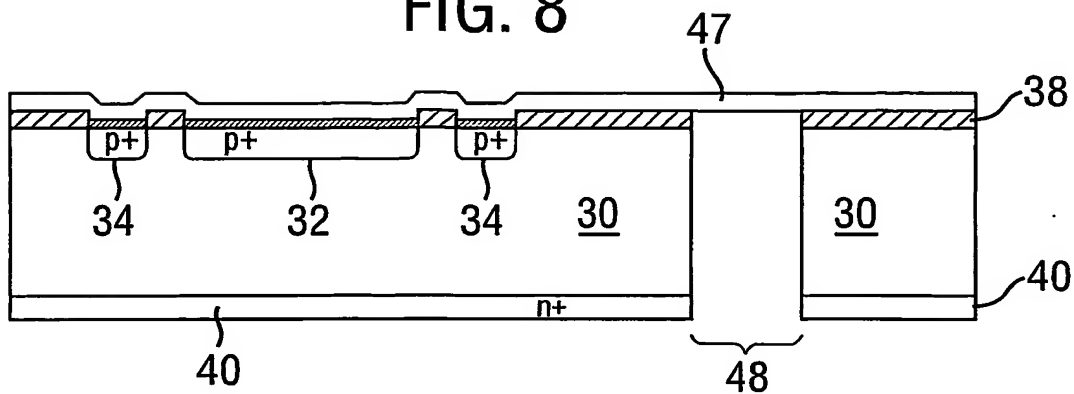


FIG. 9

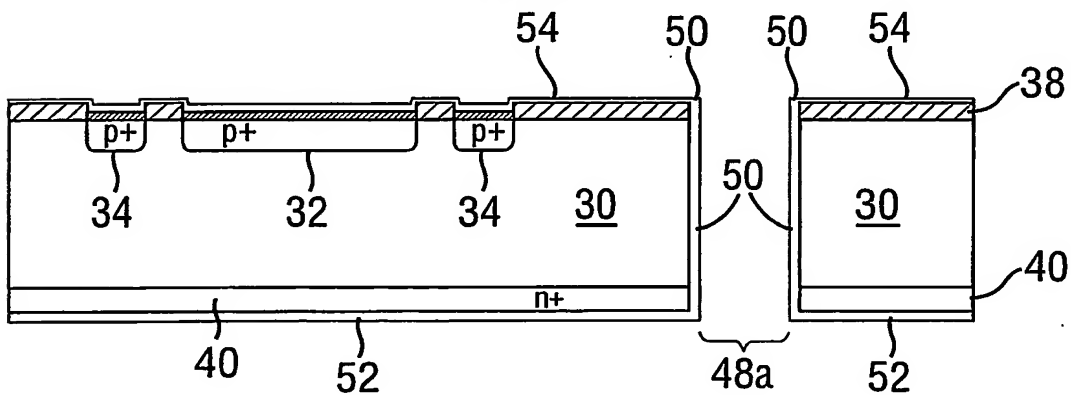
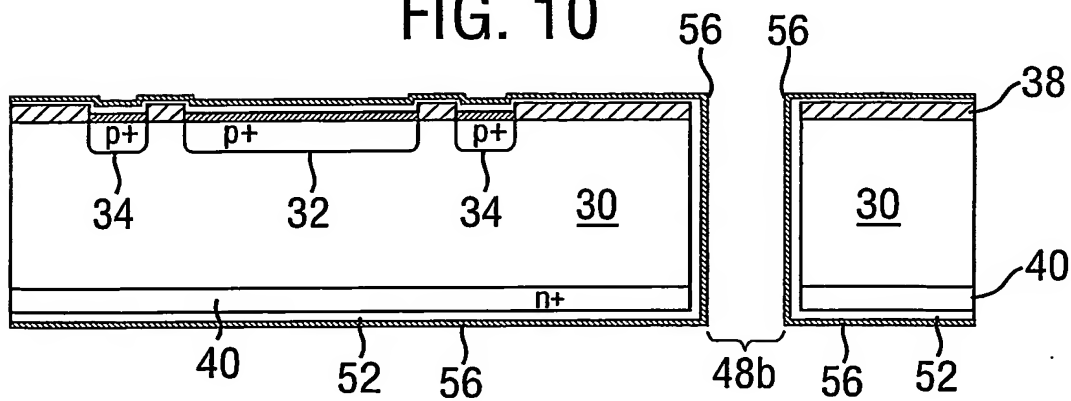


FIG. 10

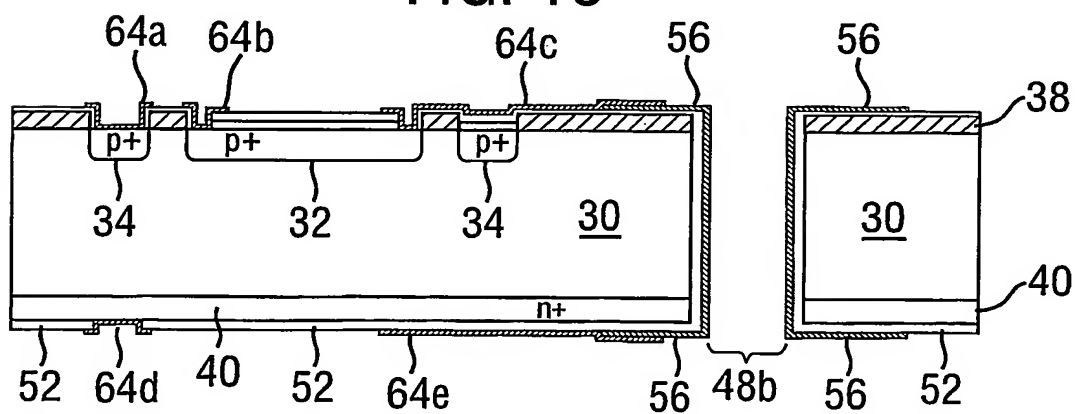
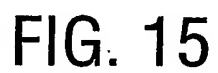


[illegible]

FIG. 12

A cross-sectional view of a semiconductor device. The device consists of a substrate 40 with an n+ layer 52. A central barrier layer 48b is formed on the substrate. On either side of the barrier layer, there is a region 30. The left region 30 contains p+ regions 34 and a central region 32. The right region 30 contains a central region 32 and p+ regions 34. A layer 38 is formed on top of the regions 30. The barrier layer 48b is surrounded by a layer 56. The regions 30 are also surrounded by a layer 56. The barrier layer 48b is surrounded by a layer 58. The regions 30 are also surrounded by a layer 56. The barrier layer 48b is surrounded by a layer 56. The regions 30 are also surrounded by a layer 56.

[illegible]



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FIG. 16

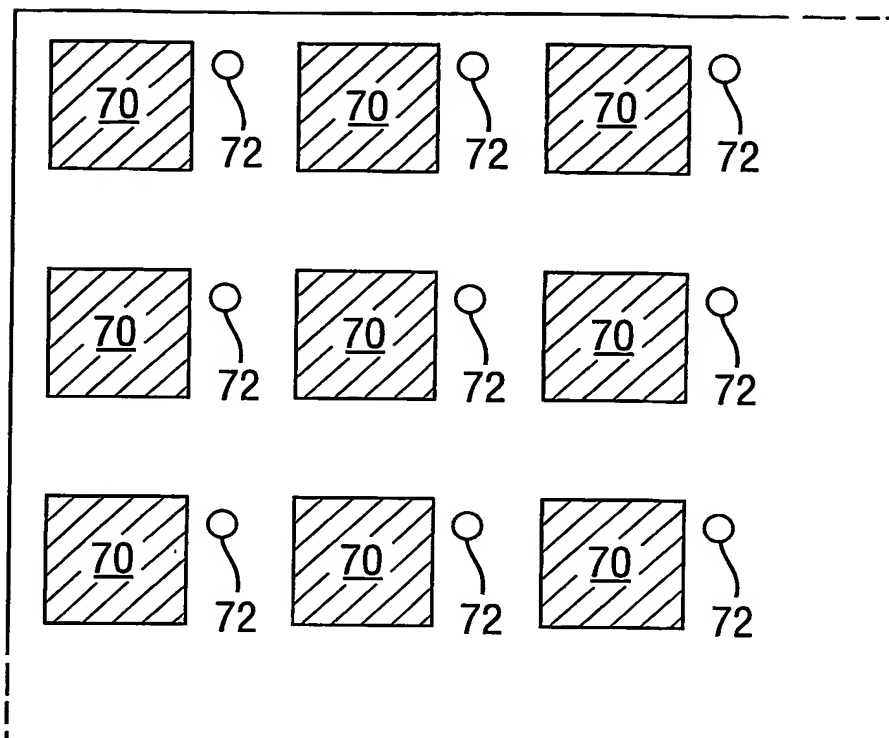


FIG. 17

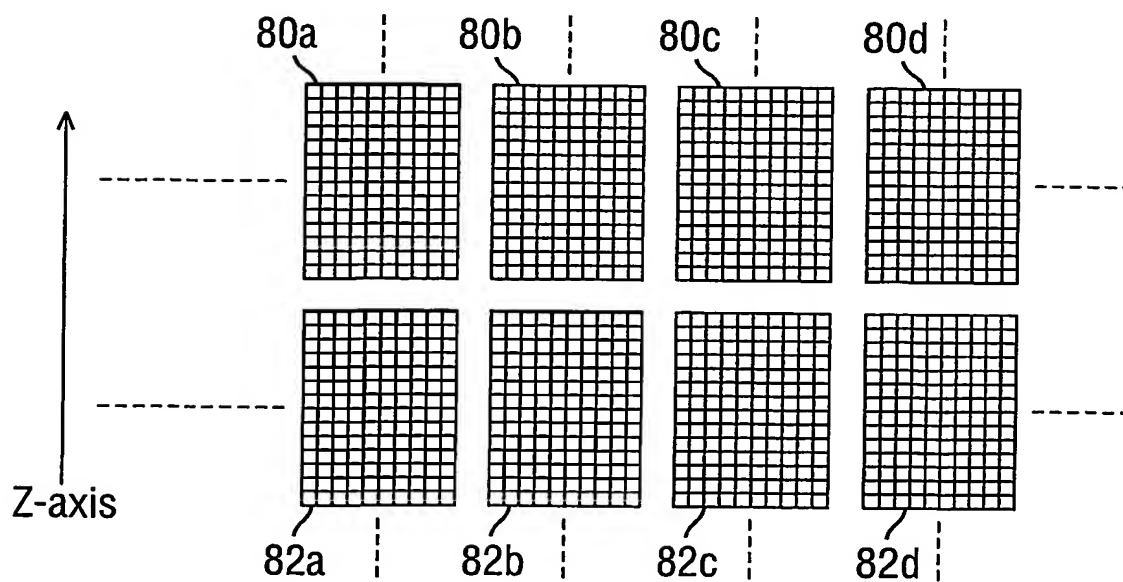


FIG. 18

